

**Bio – Microelectromechanical Systems**  
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**Module No. # 01**  
**Lecture No. # 40**

Hello and welcome to the microsystems fabrication laboratory. I am Shantanu Bhattacharya and I will be teaching today, I will be I will be demonstrating some experiments on photolithography, which is a very essential component of mems, for mems fabrication essentially.

So, let us go step by step in this, the first thing I would like to enhance and like to emphasis in such a laboratory is that you have to be really maintaining that cleanliness. And there is certain of tire, which is useful for a processing. And basically one needs to cover in to almost entire portion of the body and take the proper safety measures, so that a particular operator inquisition who is doing the experiment is not affected and also the experiment is done in a dust free environment.

So, let us look at the components one by one. This right here is one of the fundamental components used in such a laboratory, it is known as the fume hood. Essentially provides the class thousand clean spaces or clean area, which is just underneath or behind this particular. There is essentially a blower unit, which circulates and causes laminar flow of air inside this particular hood, so that typically all the dust which is around goes passes through set of hepa filters and the air is recirculated back. And there is absolutely no entry of dust particles from outside into this the clean space, most of the dust particles exit because of this continuous laminar flow operation.

So, other components, important components of the fume hood are basically and air track, compressed air track, which is kept for the purpose of cleaning wafers. Once we process these wafers, there is essentially a water connection, which is used for again washing samples as you do the processing. And the very important component, which is useful or which is the most, which is the primary component, were all the processing is done is actually a silicon wafer. So, the silicon wafer is commercially manufactured by only a few manufacturers all around the world, one of them being memc, which is

located in saint Louis. And essentially the wafer manufacturers have standardized processes, wherein they produce different diameter wafers and including 3 inches wafer or 4 inches, 6 inches, so on, so forth.

Now, this right here is such a package or a box, which comes from a wafer manufacturer, and it houses about 30 to 40 wafers in one of such packages. Let me give you closer look as to how we wafers really look like. Wafers are all stacte as you can see here in this particular fashion, and this again is packed in a super clean environment, that there is absolutely no dust on the wafer surface.

So, what we do right here is first take out a single piece silicon wafer, and I would like to illustrate how that wafer really looks like. So, if you look at such a wafer, so as you see here in this particular fume hood, we have several components which we have kept inside. Normally in order to maintain the cleanliness of the process, we use these aluminum foils, which we can see here is the silver foil, which is actually a clean surface and it is reusable.

So, it is actually a onetime use and throw bases, we can I can actually you know cut several pieces and cover this area and keep it as a base, and all the process is typically would happen on the top of such a foil. These components as you are seeing here, some of the glassware, which is around are these squeezers, which are meant for handling such wafers have been already cleaned prior to this and heated in an oven, so that you get of all the water around it, so they are actually adequate for handling the silicon wafers.

So, the first thing I am going to do is to actually unload a wafer from its box, and make a separate container or take a separate container of the wafer box and transfer this wafer. As you seen have here, this right here really the wafer box, which is meant for containing a single wafer for micro fabrication. It is very important that especially when the wafer is moving between work stations, we need to cover the wafer adequately so that we do not have any contamination as the work pieces moving between stations, so in coating.

Basically, the first thing we have to do here is to transfer the wafer from this box into a separate carry box, which is meant for holding just the single wafer. One of the reasons why we do that is because we have to actually really protect the silicon wafer, especially when it is transferred between different workstations.

So, this is a carry box which is meant for that purpose, where in there is a lead and then there is a small filter paper, which is covered at the bottom and this is used for handling wafer between workstations, particularly during various process steps of photolithography. So, we also use these aluminum foils to make a super clean flooring while doing the processes, all the components like this glassware as you are seen has to be thoroughly **you** washed and clean and then dried in an oven, so that there is no moisture, because essentially micro fabrication is a lot about cleanliness.

And so we lets to transfer the wafer from the box here, as you seen this is the wafer box, this process only has to be done within a fumour, because this prevents the chances of wafer getting contaminated by the dust particles of the air. So, we take a wafer out using a tweezer as you can see here, tweezer also is a very clean tweezer. And **the** essentially we use this box to load this wafer and later on all the handling will be done using this particular box and in the subsequent process steps and then cover this with lid.

We have closed the silicon wafer box and keep it in the separate area, one of the reasons is that we have to be extremely careful while having silicon wafers, because they are very fragile and essentially can crack even on little impact of press. So, we have to make sure that this wafer box is far away from the experiment setup that is the main box is far away from the experimental setup.

So, the next step basically is the clean wafer. Although, it is a very very clean, but we still **to** need to do a surface treatment of the wafer, so that number one it can made hydrophilic, number two is that whatever organic contamination is there on the top of silicon wafers it gets removed.

So, one of the methods of doing that is by using an acidic solution called piranha, which is essentially a mix of hydrogen's  $H_2OSO_4$  or sulfuric acid and hydrogen peroxide. Essentially piranha is prepared by mixing three parts by volume of sulfuric acid with one part by volume of  $H_2O_2$  hydrogen peroxide. It is a highly exothermic process and results in a lot of heat release and fumes. Once the solution stabilizes a little bit after mixing, typically use glass rods to stir the solution and put the wafer on the solution and clean it for 7 minutes, about 6 to 7 minutes. So, were everything, which is organic on the top goes away and then the idea is to **kind of** extract the wafer back and rinse it by using d i

water for few times, so that you can remove the acidic impurities and then dehydrated in the oven inside at 95 to 100 degree celsius.

So, let us look at that process now. Piranha is a very dangerous processes **you** as i have already illustrated and therefore, you need to use special protective covering, we are already wearing a safety glass as you seen before. Now, what I am going to do is to wear a set of polypiline gloves, these are **as a (( ))** essentially and highly anticorrosive. And it essentially prevents any kind of a damage or contamination to the operator in case of spillovers.

As you see here, you can just wear it over the secondary gloves that you're already wearing, **and** which is the clean gloves for doing processing. Once this is worn, we are almost ready for preparing the piranha solution.

So, what we do is basically pour about, in this case about 90 ml of sulfuric acid, 98 percent and you can see this is a very very dangerous chemical and it has to be very carefully used. And then, will mix about 30 ml of hydrogen peroxide, so what we do here is the following, we use this spiller, all the spouring etcetera over this drain, so that in case there is spill over everything goes down the drain.

So, essentially opening this sulfuric acid bottles is also to be done very carefully. You use these clubs, so basically you open the acid bottle and keep the cap in safe place, safer area. And essentially now what you do is, basically take this bottle and pour it in this beaker here very carefully and very slowly. As you seeing here pouring, this is not a very easy job, doing just about 200 ml and essentially again keep this back in its place, cover this properly, so that there is no chance of a spillover. And essentially close the lid and we need to actually do a secondary measurement to ensure that the volume that you're using is proper. So, use a machine cylinder for that and we need to pour exactly 90 ml here. So, what we will do is will transfer this sulfuric acid into this measuring cylinder and go all the way up to 90 ml.

So, is just about to complete now. So, we take a new container, in which we had prepared a piranha and slowly pour from the measuring cylinder the sulfuric acid. One thing we have to ensure is to identify the components which have already been used for containing sulfuric acid, because we had washed them later on properly, so that there is no risk of any experimental getting burned because of improper usage of that.

Now, we have to pour about 30 ml of hydrogen peroxide, so this right here is the container for H<sub>2</sub>O<sub>2</sub> to and the reaction is essential in equilibrium reaction with their lot of hydrogen ions and hydroxides which are generated. And essentially it is an equilibrium process, which quotes a layer of hydroxide onto the silicon dioxide, the nascent oxide surface and also creates a lot of heat.

So, basically we need 30 ml of hydrogen peroxide, so you open this and pour exactly 30 ml of hydrogen peroxide into this secondary container here, and keep it separately in this particular zone. We close this because it is a highly volatile material; it is kind of evaporates and so we need to certain that it comes back in its safe zone.

So, after we have independently poured this, we had to mix these two chemicals together in this beaker. And what I am going to do is to now turn on the fume hood essentially, because this is a very very exothermic reaction and essentially we have do also pull down the cover just about to a level, where you can just put your hands inside and do the operations.

So, essentially now will be pouring the hydrogen peroxide into the sulfuric acid, this is a very critical part because this may actually explode. So, as you see when you pour the material, there is immediate reaction which takes place and there is a lot of fumes which are generated as you can see. And this fume has to be done in a very very close environment and we have to wait for some time till this fume actually disintegrates or the appears totally and piranha is made in that process.

So, as you can see, the fumes are slowly settling down, because essentially it is a very very highly exothermic reaction, so what you do now is to actually use a glass rod and stir the solution very well, so that the mixing between the hydrogen peroxide and sulfuric acid takes place rebels. And then once this is very... and mind you this is the very hot chemical, essentially you have to be careful when you are pouring it into the separate petri dish as I will just illustrate in the next step.

This is a glass rod you cannot really use any other metal rod for doing this, because the acid immediately produces the salt from the metal and it also deposits the metal and takes it off. And you know in the process it gets contaminated, so you have the always using glass rod or glass container for doing this piranha making process. Once this is made, you rinse of the excess piranha on the glass rod and keep this rod that include the

container for H<sub>2</sub>O<sub>2</sub> and this would later on clean before we can reuse this again. And so what we now do is essentially take this piranha, what we have prepared and then pour it over our silicon wafer, which will be keeping in this particular petri dish separately.

So, what we do is essentially we take our wafer, silicon wafer and open this and clean. In order to clean this wafer, we put this wafer back over the petri dish here. As you can see here, we are putting the wafer in this petri dish and once we pour the piranha, we can no longer use metal tweezers for a handling this wafer, so will have another separate effluent user for doing this wafer handling once it is out the piranha for washing and rinsing.

So, now, we slowly pour this chemical **the** piranha over this wafer and you know it is extremely hot, and as you can see, **and** essentially it also fumes as you pour it. And immediately if you can see, there are the organical contaminations over the silicon surface, has been immediately removed. And we store all these container later on for cleaning and using it for different applications. Now, we keep this close and wait for about 10 to 15 minutes, so that the wafer can totally get a rinsed.

So, these as you see are now teflon coated, these tweezers are tips which are coated with teflon or they can be complete teflon tweezers, **which we are** which we can use. So, what we are going to do is to provide normal rinsing using distilled water as you can see here, which is resting in the flask of this particular piranha clean wafer sample. And then this would be followed by another wash of d i, d i is to water, so that it gives the super clean surface on the wafer.

So, what we do **you** basically? Pull it out very carefully, because essentially this is all acid coated now, one has to be very careful and then hold this over this edge and rinse it inside this with water and rinse it on both side as you can see, all the water should typically go and rinse on the acid of the surface of the silicon wafer. And essentially, once this is clean, the in the next stage what we do is take this d i **of** water and slowly rinse it on the surface of this particular wafer. As you can see here, this is actually a squat bottle, which is squarding away the d i on the top of the silicon wafer.

So, essentially after completely rinsing it, you basically try to just change its holding location to a different area, so that you can rinse of the acid in the particular area where it was held before and this way you can clean the whole sample. And essentially you can

see now that the sample is more or less thoroughly clean, thoroughly washed **and** as the super clean nature on the surface.

Essentially after this step, so wash that, that is totally cleaned, we need to now use the compressed air to dry this particular wafer, but before doing that we need to take care that the acid etcetera, which is actually kept in oven needs to be kept away, so that there is no squarding of the acid in general, so now you take it.

So, this is basically an air nozzle, it actually sense and compressed here. And what we are going to do is to actually slowly use this nozzle to clean of the surface water as you can see here, slowly from the surface. So, essentially you have to move this thin firm of water in the clean hood away from the sides, so that you are actually left with a clean surface of the wafer, clean shining surface of the wafer. And there should not be any water drop in this manner on the surface, typically all the water firm should go away from the surface. Similar cleaning has to be done for the reverse side and I am going to do that as you see here, seeded from the compressed nozzle side towards the other side and it is then rinsed of the surface by squats of compressed air as you can see.

So, this now really **is a** is a super clean surface for lithography to takes place, so we put this sample, this clean sample back into the wafer box as you can see **since** and then we will actually do a heat treatment of this particular wafer, so that it can get read of all the water from the surface and **that may** we have a completely dehydrated surface. We need to coverage at this stage, because the moment we move it out of the clean area, it can again become dusted and the contamination of the surface may happen, so this is how the kidana cleaning process of the wafer is done.

So, basically what we do now is to take this wafer that we just made super clean using piranha process and take it to an oven. The oven basically that we are using here is a gravity fed convection oven, which actually **a if** based on the principle of free convection, the set of heat coils at the bottom and there is a current of air, heated air, which actually makes the temperature uniform. There is a p i d base controller using a thermocouple with somewhere in the floor of this particular heater.

This right here is that oven, so what I am going to do is to illustrate a little bit about this oven and then basically use this oven to heat, dry the wafer surface. So, basically if you look at this oven really, it is a shield oven as you can see, **the** there is a fan which actually

does force convection along this whole area. And essentially the wafers are kept at various levels, thermocouple is somewhere at the bottom that is one disadvantage of this particular type of oven, because sometimes is not a very good indicator of the temperature that happens.

This right here is the controller; it is based on proportional integral differential controller. So, as you see here, there are two different readings, there is a set point and then there is a variable point when the temperature goes up and down base on one of this set point is or it control. Basically if you can see here, right here, there is a set option, so you press the set option and then take this up arrow or down arrow. And as you are seeing the figure here, which is the s v or the set value is varying 89.3, 0.4, 0.5, 0.6, so on, so forth.

So, we take this all the way to about 100 degrees, which is important for proper hydration of the wafer surface and once you reach 100, you basically leave the set key and this is now set at 100 degrees. So, this temperature, which is also the **proportional** proportional integral differential temperature, is actually slowly equalizes the set value after a while. And basically there is some kind of a flickering around the set value, it does not flickering **and** slowly attains the set value point.

So, basically, now, as you seeing here, the variable values **have** has almost reach 100 degrees and this is enough time for our wafer to get loaded inside and get dehydrated. So, what you basically do is, essentially take the wafer box, which we pulled out of the fume hood after the piranha clean and then basically put an aluminum foil on the top of one of these shelves and then slowly load our wafer sample so that we can get it heated and remove any water if present on the surface of this wafer. And the whole idea is to have a perfectly dehydrated surface of this particular wafer, so that it can be good for adhering to the photoresist that we essentially spin coat on the top of it before doing photolithography.

So, we keep the wafer in the oven **the** for dehydrated for about 10 to 15 minutes, at about 99 to 100 degree celsius. The next step is to unload the wafer and start doing what we call spin coating of the photoresist. So, what I am going to do is to just unloaded and carry it back again. Please note that we are using a same wafer box for carrying the wafer. Again **from the** for the constraint that it should not get contaminated while going between operating stations, so we slowly use the tweezer, which was again used for the



other processes. This is again a clean tweezer and we **are** slowly pick up this wafer from the oven, transported into the box here and **in** convert this or cover this with the lid. So, basically now we have a clean wafer, which would take to the next station, which is actually the spin coater, where will be doing the resist coating.

So, the next stage basically is spin coating the photoresist. And for spin coating, the first thing is that one is to take care about **is** the grade of resist that one is using. There are many manufacturers of resist in the world, we will be doing negative tone photoresist here, which basically means that wherever light or u v light is used for exposure of the photoresist fell, there would be a general cross bonding among molecules and the resistance back and the portions which are unexposed can be developed off. So, really what you have is, basically small features translated from masking mask design onto the resist surface. On wherever light has fallen through the mask window onto the resist, the features remain, the other portions of the features go away after developing.

So, the first thing that is important here is to download the specifications of the particular grade of resist that you plan to use. And what we normally do is we use a resist from micro cam, which is actually a resist maker. And essentially we are using a grade of resist called 20-25 s u 8, which as at certain viscosity. And what the resistance manufacture really does, he really puts together an experimental curves for this particular viscosity and so, basically what he determines is what is the r p m at which we should spin the resist, so that a particular thickness can be achieved and thickness defines whether the r p m is really the thickness of the feature that we are looking at.

What it also does is, it actually mentions about the temperature steps that you need to include in order to process the resist, once it has been spin coated. And also after the exposure, it also mentions specifically about what is the exposure dosage which is needed and what is the time for which the resist needs to be exposed, so that it can have enough crosslinking and cross bonding. Just at the outset I said, this process of photolithography is about developing cross bonds between different molecules and that is essentially driven by reaction chemistry and has a certain range. So, it is very **very** critical for us to be able to determine how much temperature is needed, what is the time point or what is the time of holding for that particular temperature, **also** we also need to ascertain what would be a typical exposure dosage for all the molecules within that small window to get exposed, so that they get cross linked very well.

So, essentially I would like to go ahead and make features, which are about to 20 or 29 microns thick and for doing that, if you will see at this grade sheet, you basically get these curves here, where it talks about what is the r p m on the x axis here and what is the corresponding film thickness that will be getting. So, when we are using a certain grade here, which is mentioned in this table here as you see so s u 8 20-25, which is the lowest grade. Here, it is really corresponding to a curve, which is the least this curve essentially here. And so corresponding to about 20 to 25 microns, what we find out is the r p m that we would need for this is about close to 3500 r p m.

So, I am going to in just about a minute set up, the spin coater that we have here, and tells you about more about how to program this machine, so that you can have the particular spin speed and a particular r p m and you can also be able to hold it at that spin speed for certain amount of time. This right here is what we call the spin coater, essentially if you look into this machine closely, you have a spin stage, which is represented here, which is here in this area, essentially the principle is to use vacuum for holding the wafer on to the spin table.

And if you look closely into this particular area, you have these grooves here, which are actually criss cross and they are placed over the whole periphery of this stage. And the purpose of these grooves are that there is a vacuum track immediately below this, which is connected a vacuum pump underneath this whole system and essentially the vacuum propagates all the way up through this small center hole here, and then also propagates along these grooves, and kind of wholes hold to together the wafer on the top of the surface.

What is also important for me to tell you is that there is a control, which is here, for which we can actually use for flexibly controlling the spin speed, also the amount of time for which we can hold at a certain speed. And also what is very critical for different waves of the resistance is that the acceleration at which you can rotate in order to achieve a certain speed. So, here in this particular example, but, I will be demonstrating as per the resist, the manufacturer specifications, the spin speed that we are using is about 3500 r p m, and also you know the spin speed has to be (( )) with the acceleration of about 300 r p m per second. And what it also mentions is that you have to hold at a certain spin speed for about close to 19 seconds, for the spin coating to be uniform.

I would also like to illustrate here that the resist being a thick material, needs a little bit of time for uniform coverage over the whole surface. When we are talking about the circular wafer, what is very important for us to understand is that **the** first of all the resist that you are putting should be sufficiently covering the wafer, so that **you once the** so what is also very important for me to illustrate here is that, really what we are doing is to spin the resist on the top of this circular wafer, which is about 4 inches or so.

And we need to be able to **a** certain what is also very important for me here to illustrate is that, **you know** the particular spinning operation should be able to adequately cover the whole wafer surface. This is a circular wafer of about 4 inches diameter and the goal here is really that the resist should not have any gaps or any islands on the surfaces as your spin coating it.

So, you have to **a** certain how much area you need to initially pour or cover, so that you have enough resist, so that essentially spinning process is nothing but centrifugation, there is a slow coverage of the surface of the resist, which have been poured somewhere in the center by centrifugal forces. And so the whole idea is that you cover adequately and give adequate resist, so that when it goes radially in all directions, it should be able to have uniform coverage on the surface.

So, for doing this, what would we need to find out first is how to set up the controls in the particular spin coder and how to control the r p m time, the r p m per second rates etcetera. So, let us look at that in our next step. And corresponding to this program number, what all steps are there in the program are illustrated just this in this particular region.

So, as you are seeing here in this, in the run mode, the step one of the program illustrates that their would be an r p m of 3500 r p m, which is attained at an acceleration of 300 r p m per second and the time of hold for this is about 180 seconds. And this is with an option of vacuum operated, so that the wafer is pulled down while the spinning happens. And then finally, you have to somehow change this program to suit your requirements. So, what we essentially do is to first use the program mode here as you can see to go to the number of the program. Suppose you want to make a new program here, so we find out **the** or we give a new number here, let us say we want to make program 7 and then we try to see **or try to see** or try to illustrate what is there in program 7.

So, go to the mode option here, so basically what we now do is after we have entered program number 7, we enter this program and then go to the mode option, so that we can get a detail of what all steps are involved in this program. So, here, really the program is about step one, and **on the** it is a one step program **and** followed by the end of the program, right, so it is one end. Now, what we do is basically move to the next option here and we get this r p m, which is actually two thousand this particular cases as you can see.

So, what I am going to do is to change this to 3500, which is our requirement and we can actually hit enter here for the system to take this. The time for which we need to coat this r p m is about 90 seconds, so we do 90 here and then enter the data. And the next step is what all revolutions per minute, per second, we need this speed to be, so we put the value for the acceleration 300 and essentially enter this value. And for our condition, we need the vacuum to be on while the spinning is happening, so we just do whatever is the default and that completes pretty much the program.

So, all we need to do is to now actually put the wafer back to the spinning stage, after which we will be doing the run operation. So, what I am going to do now is to actually simply load the wafer onto the spin table and then we have to also see whether the wafer is actually centered, which I will do little bit later. And what I do is, I just turn on the vacuum, you can see this light, the green light appearing here, which means that the wafer is now firmly held to the surface and it cannot come out and it is basically clamped pretty firmly onto the spin table.

So, now, it is almost ready to rotate and spin, and essentially code whatever is there on the surface of the material, so we would like to also have a loop, as whether this wafer has been centered. And the best way to do that is to close the lid and see from this transparent section on the top, whether this wafer is really at the center of the spin table, in case it is not, then you can switch off of the vacuum and again and again change the position in a manner, so that the wafer can come pretty much at the center of the spins table. And the thing is which we are ensuring here is that they **are** should not be any wobble really of the wafer and it should actually rotate **and** its own axis and so it should rotate at its own axis and **the** that can ensure that there is no underutilization of the resist, which is at the very center of the particular wafer.

So, basically we have now placed the wafer and essentially what we need to now do is just turn on the vacuum here, the light would come on as you can see here, this is in the on mode, so basically the vacuum pulls the wafer, so that it can sit on to the spins table. And then we have **do** also seen whether the wafer is center on the way to do it, basically close the late of the spin coat and turn this r p m on, so the system actually starts rotating and see from this top transparent area, where there is in wobbling in the particular wafer.

Now, as I can see here from the top, the wafer is more or less center and there is very less wobble, so I really did not do anything about position of the particular wafer, so I am going to filled this on to see the wafer is moving inside spinning and essentially there is very less wobble and we can do with a this kind of wobble.

So, I am going to now spin coat the photoresist on the top of this wafer by pouring the resist and then doing all this execution of the r p m cycle. The moment the resist is spin coated, we also need to take this now for the twins step heating process, which I am going to describe a little bit.

So, the resist as i told you needs to be heated and one of the purposes while heating needs to be done is that there is a solvent, which is really a career solvent for the resist **molecule... to way resist**, it has really an epoxy resin, which is dissolved in a career solving, which is actually cyclopentane. And essentially the purpose is really to transport the epoxy uniformly over the surface of the wafer in the spin coating process that we solve **last** in the last step. And then we need to get read of this solvent, because essentially that would ensure that the resist film is stable, it is hard enough and it is a kind of equibonded.

And before doing a expositor it is very critical, because the mask could set on the top of the resist, and therefore, if there is some unride portion or uncured portion, the resist is going to the damaged, and that is something that we do not want because that would mean that the surface of the micro features that we would result, I mean **that** it would result in, it will also be damaged because of that process.

So, we need to certain that the resist**ance** is fully cure before taking it to the next exposure step. Now, I would like to illustrate one fundamental factor here, is that we all know that because of heat edition, there is a thermal expansion and this is a thin film we talking about, the resist really a thin film. And so they may be a **rapid** due to rapid

heating or rapid cooling, there may be a tendency of the resist film to vary over the surface and create undulations and that is something that we want to avoid, because we need to be as much planner as possible for the surface structure integrity to be maintained. And so it is really a good idea to heat resist in a stepped manner, heat it to the lower temperature, may be about 65 degree also and then heat it to a higher temperature, so that it is an adjusted enough and there is one undulation of warping of the film as such.

So, therefore, we use hot plates for this purpose, here as you see, in this particular station, there are two hot plates I have. They have been pre heat to the temperature of 65 and 95 degree Celsius and each of this steps would have a certain time associated with it, so the spun coated resist on the wafer would basically brought in and this plates would be used for heating these, so that we can get a cured film **the** resist on the surface.

Basically close this and just start the spin coating process and let the film that we have set **kind of** spread over the whole surface and create a thin film, which is about 20 to 25 microns of this resists on the surface of the wafer.

Resist is actually spun coated now and we have to be very careful about removing the wafer, we have to hold it from a thin corner at the size, because that is typically the area, were there should not be any designs and structures. We will just use a little bit of tweezer space for holding it and be extremely careful about handling, because mind you at this stage the resist is actually a kind of liquid nature, we have not cure and before **the** curing the film is like tacky and then if you have any stresses or any impact on the film, it is going to create a huge difference and make the film not behave properly.

Also, we need to ascertain of one basic fact that the table that we are using for keeping or lining our hot plates should be perfectly parallel to the ground, because otherwise there may be a possibility of resist running to one side, thus creating a thicker film at one end, which is highly undesirable, because you want a uniformity in the film thickness, which also determines the size and nature of our structure and feature.

So, essentially, now the program has stopped and I am going to slowly pull and I can see here, there is a thin film of resist on the top of the surface, I am going to actually take the wafer box here and then slowly use a small amount of space. So, first thing we need to do is to close the vacuum, so that we can decouple the wafer from the spin table. We take

a very close, a very small portion and bite allowing with this is tweezer on that portion and then slowly transfer the resist coated surface onto this wafer holding box. And then once we have done it, we actually cover it with this **this** cover here, not press it very tightly and then slowly move towards our next step, which is a hotplate and keep it on the 65 degree set hotplate and wait there for about 3 minutes or some.

So, I am going to put this wafer now on the top of this particular hotplate, which has been setup 65 degrees, so for doing that we have to be again very careful about pulling this resist coated wafer out. We use the exact same area as we are used before for **a** holding just **in** a small edge or a small corner and then keep it on the hotplate. We have a stopwatch with us here, at this particular stage we would like to operate on the stopwatch by setting in at 3 minutes and then starting to operate this. And basically the idea is that this will give alarms at the end of 3 minutes, we need 3 minutes heating time for this particular process set of 65 degrees. And then, we will go to the next step, which is another 3 to 4 minutes on the 95 degrees, so this **is a** watch is now reading about nineteen second or so.

This is actually is an alarm system, it would tell you in advance, as the time is over, it will have a beeping sound from which you can actually figure out what is the exact time for which the resistance thing needed. Thing about micro fabrication is that you have to be very careful about the exact whole temperatures; this right here is an illustration that the time is over. So, what will do is, will go ahead and pull out the resists now, the resist coted wafer now. Again, the same precautions need to be followed, we need to hold the resist from a very **you know** small corner here and then slowly put it over the surface that we **want to meant** want to put it.

So, I am going to now transfer this resist coated wafer onto this particular surface. It is almost, it is always a good idea to actually coat the heated surface or it hold the heated surface at the room temperature and let it come back to the particular ambient room temperature for **you know** the film to have a least possible undulations and warping **is possible**. We will just cover it in case there is any dust accumulation on the surface, the another thing I want to point out is that the environment **in this** in which the scoring process is carried out is a very clean environment, we estimate, we plan to actually do these things typically in clean rooms, where the particle contamination may be as low as

about **us** close to 2000 p p m or 100 p p m depending on what kind of feature sizes you are using.

So, essentially we will hold this for some 5-6 minutes till it equilibrates back to the room temperature and then we will actually use the second heating step of 95 degrees and put this resist back again for about 5 to 6 minutes for the full curing action to take place, after which we will do the U V exposure of the resist using the mask.

So, after the **(( ))** its location and put it over this plates, which has been set to a temperature of 95 degree Celsius, we start on the stopwatch and set it to about 6 minutes time, so the idea is that **you know** after 6 minutes, as **we sulfuric acidic** hear the second alarm, we should be able to pick this up and then again let it equilibrate back to the room temperature before the exposure process.

**Ya...Ok and the wafer would go there.**

**Ya ...Right, I do not need view this, but we can say that you know that has to be done**

**Sir, how will you ensure that (( )) height and on that**

**I see ok**

So, we are nearing the end of time that it takes, there is an alarm bell now again. So, what we have to do is the same thing, will pull back the wafer from the surface here and then put it back again, **on the you know** use just a small area here to keep the way for hold **the** wafer through the tweezer and then put it back again **or** its resting place where we will use a little at a time for equilibrating it back to the room temperature. So, we are now ready after this temperature is a close to the room temperature to do lithography on this particular wafer.

So, essentially this is called the photo lithography equipment and this is used for exposure of the resist to very characteristic frequency of light, mostly in the u v area. Essentially here what you do is to use something called the hard mask, which you can see here, right here, this is actually a glass cromask, where **you can see**, very closely if you look at some of these features, really are at the micron scale. And these has been made using a laser etching in a film of chrome that you **(( ))** that side, this particular side, which has the coating really sits with the wafer, being aligned with the wafer, because



otherwise if you have the other sides sitting in proximity to the wafer, there are diffraction effects. If you see the thickness of the mask, this is made in a glass plate, which is about close to 900 microns or so thick, and therefore it is a very good idea to have the metalized **the** surface in proximity to the coated wafer 0.9 mm or 900, is good for a beam of light to get hugely diffracted. And therefore, if suppose we what to do the other way round with this side, the glass side sitting on the top of the wafer, **in** the feature that would be typically looking at would be much more in size because of the diffraction effects.

So, what I am going to do now is to tell you how to use the lithography setup to actually do alignment and exposure. So, here, we have something called the mask holder, which is actually this region here. The mask is really sitting on the top of, on the bottom side of the surface of this particular holder and it is actually facing the wafer which would be placing somewhere here. This is the wafer stage and the idea is to be able to precisely align the hard mask over the wafer surface.

So, in order to do that and what we do is to **kind of** lose these particular points here, there are four such screws and then slowly pull out this part from the machine and essentially as you see, this really is the surface which holds this particular hard mask. And there is a stand for this application or this this mask loading, you have to put it right in that particular spot, it is like a jig and it ensures that there is no unnecessary toppling or falling down of the mask holder.

So, we take the hard mask and this mask to be pre cleaned, this of course is the pre clean sample, so what you should normally do is to put a liquid compress nitrogen or compressed air and blow **tight**, thoroughly so that there are no marks. Suppose there is some finger mark or something which comes on top, so you could use a small amount of acetone and wet kimwipe and then slowly rub over it and then wash it in ethanol and then clean it using dry air, dry nitrogen or compressed air.

So, what I am going to do is to actually aligning the marks in its place here, **and slowly** so there are two slots really for that purpose and I am going to actually make it face down, therefore the chromium side has to be facing the wafer surface. So, this is actually given by this dark brown region of the mask, **so I am** so I slowly put it inside the mask holder. And then, basically this is only a passive gripping, we need to make it active by

using vacuum, which can be operated by using this controller, turning on the controller, and the controller power on above and then actually use ah the wafer holder and the mask for the vacuum to be operated on to the mask.

Now, if you see, the mask really is held very firmly, **now we have** it actually mounted and well connected with the vacuum from the system. So, what we do is we take this wafer holder out and it is pretty much firmly gripping to the mask now and there is no possibility of the mask following as you can see, so we go back into its possession here, and then try to mounted in a manner so that you can actually bolt this mask holder onto the top of the wafer surface.

So, there are four bolts for that purpose, actually try to align them with the bolt which are there in the top of the mask holder. And essentially you can actually now use the locking mechanism to ensure that they firmly get locked over the wafer surface.

So, what we do is now actually after mounting this properly, we need to actually bolt it firmly, so we are going to actually use these set of screw heads to ensure that the there is a **there is a** good contact between the holder and it grips really good on the surface. So, we are going to just ensure proper gripping of the holder, of the mask holder onto the surface of the stage. The stage is **by the by** going to move along with this whole mask holder to the exposure zone, which is underneath the scope, as I will be showing you just a little bit and it has to be having a tight grip for the purpose of proper alignment with the wafer on the surface.

So, what we are going to now do is to actually move this exposure stage, the scope actually from its current location to near this, over the mask holder, so that I can have this zone here for wafer loading and unloading free. And essentially, now, I take out the wafer and loaded on the surface of the chuck, which is just here in this particular region.

So, essentially now what we are going to do is, to take the wafer from its box and actually put it in this particular zone here, which is meant to do wafer holding. Again, we would like to use vacuum as a means of locking this wafer, this spin coated wafer, resist coated wafer onto the exposure stage. And this switch right here, which says wafer vacuum actually ensures that the vacuum is used to pull and lock the wafer.

I want to just check in whether the vacuum is working well, and I found out that it doesn't move anymore, the wafer is jam with respect to the stage. And then next step is actually to exposure to U V, so in the next step what we do is, we actually now align the mask with the wafer by pulling this stage all the way up to its position here or location here, and then try to actually manually bolted, bolt the holder in this place so that it does not move back. And also what we would need to do here is to actually go ahead and move this microscope stage back for the correct focus, the idea is that the wafer has to be z displaced, so that it can come in contact with the mask surface and for doing that we also use the scope, this microscope.

There is the small IR beam which is actually, this is small red light beam which is actually used for the purpose of seeing whether the wafer is really touching on to the mask surface. And so what we do is, in the first stage we move this particular microscope of the scope stage all the way to its position here above the mask and then there is a small lock here, which we used for locking. There is also a control here, where we can actually turn on the red light, which actually is now focused on to the mask and the wafer. And the idea is we should be able to move the various **the** wafer stage and we do it by moving this is the x displacement and really this is the y displacement for the scope, so the scope can position on a particular area. And the wafer stage can be moved by the control, which is there at the bottom here in this particular zone. And we can actually move the z displacement to see whether the feature onto the mask is really in focus, if it is in focus that is an indication that the wafer has touched the mask surface and that is really **(( ))** at which we should do the exposure.

It is so fine align that if you just go up of that focus point or below that focus point, it indicates either you are pressing the wafer hard to the mask, which means at the cost of damaging the resist or you are going away, that means creating a gap between the wafer and the mask surface, either event is not good for us, we have to just be able to make, adjust a close contract without much pressure onto the resist coated surface. One of the reasons why this kind of alignment systems are also called contact aligners.

So, essentially we would just like to see through this microscope stage and try to find out if the features etcetera is close. I see that there is a little bit of displacement, which is needed to be done on the z access, so that **the align** the images can be correctly focused.

Now, I think, we have really pretty good adjustment and **we can do**, we are all set do the exposure.

So, this right here is also a controller for exposure time. If you look at the resist manufacturer shielded gives the exposure do such for certain thickness of the resist film. So, what we need to do is to calculate from there using lamp power, how much time of exposure is needed for the particular thickness that we are operating.

So, **that the** because our thicknesses of the resist is about 20 to 25 microns, we can get the correct exposure at the dosage rate that this particular lamp offer time of about 20 to 22 seconds. We use this timer setting for achieving that, so that you have these different values here in minutes and you can see right now the setting is about 22 seconds here, which means that exposure would be for 22 seconds.

Now, what we have to do is after all this exposure time setting etcetera has been done, we need to take care of this microscope stage by moving it back, because now we also need to do exposure. And so, essentially I am going one unbolt this whole stage from here and is shifted slightly towards the right and in dock it in its position. And essentially that is going to give me **a you know** a through pass for the light, the **u v** U V light to go through the mask and fall onto the wafer surface.

So, this is now taking care of the mask, is there in contact with the wafer. And in order to protect the operator, there is a U V shield, which has to be installed here before doing the exposure and here all set to do the exposure. So, I am going to now actually turn on the exposure light and as you see here, the moment I turn it on, the timer clock has started, and **the light** the U V light is now falling sharply onto the wafer. And essentially **this is** the time reading here says that it is rapidly reaching 22 second mark that we had said before. On the moment that is done, this light will go off, the exposure light will go off, and our exposure process of the photoresist is complete as a matter of fact, it is just completed now.

We have to actually just unload the wafer and the mask, separate them together and we need to go for a post exposure bake next step, there I will be explaining the next step. Now, I am actually going to go ahead and turn off the exposure system, because it has been working from very long time. And now, we need to step by step do the processing in a manner that we need to separate the wafer from the mask.

So, good way of doing that is to actually go anticlockwise, so that the masking stage can go down and I can now take the wafer all the way by using contact with the mask surface. Next step would be to move or push back the particular mask holder all the way back to its resting zone, which is close to this end and turn off the wafer vacuum, so that I can pull out the wafer. And this is actually the exposed wafer which we are pulling out, we will again loaded back into its resting place, which is this container right here and we will do something called poste exposure bake after this particular step.

So, slowly you have to pull out the wafer from its stage, now it has been released, vacuum is no longer holding it and we actually slowly take it and put it back into its wafer box, cover it so that there is not much dust contamination on the surface and close it and set up the microscope back to its place here. We also need to just reverse the sequence to pull out the mask, we need to just switch off the wafer holder as well as the map vacuum and essentially need to just pull back the mask in the pretty much similar manner as we have loaded it before.

So, these bolts need to be tight, un tight, so that the lose grip on the top of this wafer holder slowly move the holder back in its place and keep it back here. And essentially move off the mask as we had done before and store the mask in its place, in its box right here. And all we can also put this holder back in its place, so that the machine is ready for the next run. So, as the system is turned off, the next stage is basically to take this wafer and do post exposure bake. One of the reasons why that needs to be done is that this really is a heat catalyzed process, if I put the exposed wafer in a room temperature conditions and keep it for a longer time, there would be a slow protonation in the exposed areas, which would create really the opening of the epoxy changes and cross bonding in the areas which are exposed.

However, I would like to fasten this process so that the overall time duration for which the lithography is completed is lower and for that we need heat based catalysis of the process. And so doing this what we really need to do is to actually take this wafer back to our heating stations and then there are again manufacture specifications of the resist, which stocks about how many minutes we need to post exposure heat or bake this using the hot plated, the two temperature conditions that we have done before.

Some are going to now actually pull out this exposed wafer, called it photoresist as we did in the last step and slowly put it on the top of this. Essentially this hot plate and the time here that we give for allow it to be heated for at the 65 degrees step is about one minute. We turn on the stop clock and essentially wait for the alarm bell to go end, so that we know that we have heated for the time cycle that was supposed to be again we have to equilibrated to a room temperature condition and then put it back into the 95 degree step, so that we can have a undulated, properly exposed and cured photoresist film.

So, time is up, really now I will show we should whatever we are want to into actually take it back again, put it back into its resting place again and then wait up till this equilibrates to the room temperature and go back, do a 6 minutes heating step in the next temperature step, that is 95 degree celsius.

Basically, now we actually put back onto this wafer surface onto this hotplate surface, which is set at 95 degree Celsius and essentially we heat this to keep this for about 6 minutes or so. And one thing very good about this process is that, if you look closely, you could really see the features coming up on the surface as you are heating using this 9, 4 degrees. Essentially the points which are slightly misc contrasted, you can you can see the different contrast there in the zone which is exposed. When you are developing using a developer solution, those are typically zones which remain back and the remaining portions which were unexposed go way and that is essentially what negative tones resist is supposed to do on the wafer surface.

So, we are going to now pickup this, the wafer from on this particular place and you know we have now completed more or less the whole exposure and the post exposure baking steps, and essentially we are now ready for the next step in the process which is developing. And this developing is important, because essentially, this actually leads to the future really getting generated within the surface.

So, I am going to just take this wafer to the fumehood and there is already a developer solution, which is actually already placed at the fumehood. There is a certain time for development, which the resist, the manufacturer specifies of and this again is the function of thickness of the particular resists, as we our thickness are in the range of 20

to 25 microns, so the resist maker specifies the developing time for this particular thickness, which is about, which is about 4 to 5 minutes in our case.

So, let us actually try to develop it another important point that I would like to mention, is that the resist which is actually leftover onto the surface while this developing is taking place and it is unexposed, kind of turns white or cloudy as you spray isopropanol. So, development process is really after the whole time duration is over, it is its an interactive process, where you kind of spray the isopropanol on the top of this surface again and again, and see if there is a cloudy or milky so with the surface. Any illustrate resist which is left over, which is unexposed would definitely turned milky and cloudy, so you have to see when by pouring isopropanol, you do not get this cloudiness anymore, which also means that your development process is complete and that gives you the best resolution of the features that you looking at on the surface.

So, one thing we have to also take care of in this case is that you cannot just simply drop of the wafer on into the developer, you have to keep on stirring the developer solution from time to time, so that there is no accumulation of the resist which is coming off, the unexposed resist which is coming off at one particular place.

The idea is to keep on dissolving it by swirling the fluid which is over it in a in a particular manner. So, I am going to do that and then after 4 seconds, I am going to also spray isopropanol to see whether this resist that. We have done is actually, totally developed and up and essentially a start the time, now is set to about 4 seconds and then we keep on giving some swirls to this developing action and essentially you have to ensure that this happens, so that you get good features on to the surface.

So, as you can see here, in this particular case, after the developing is happening, immediately after you put in to the developer, the features kind of nicely and beautifully get generated. We need to do a proper microscopic analysis later on, but this really is the success of the process, it means that whatever you are exposed is essentially keeping their resistance all cross bonded and remaining portion has been moved. And essentially again you keep circulating the (( )) isopropanol from time to time to see whether you know everything is remaining on the surface.

So, I am going to put this for the first time and see, this is another beaker that we have to put here for spraying isopropanol to see, let us pull this out and the border right here is

really the isopropanol, so I am going to see this, I see that there is some clouding action which is happened, which means that resist is still present, undeveloped resist is still present. I put it back into the solution and again try to just give it a few turns and see, so this process keeps on going on for the stipulated time and at the end of the process, we will have a really sharp distinguish features, which come out the process.

Basically **we had** in an earlier experiment developed this piece of wafer, and essentially now whatever was there on this mask has been transferred onto this wafer using the process of photolithography. And essentially these is not the end of the process, because we really need to a measure and calibrate, and be able to see the microscopic features that have been in printed on the top of the resist, which would be using later for our purposes. And for doing that we need something which can create a high magnification object.

So, in our laboratory here, we have this microscope, is actually inverted florescence microscope, but it does have an option of being able to image using the bright field, dark field imaging. And essentially **the** this microscope is from Nikon, there are certain manufacturers of these optical devices, they are precise, this needs to be arrested on a vibration field table as you can see. And I would like to describe at the very outset little bit about the microscope and how we do the imaging modality.

So, here, in this particular zone, these are also known as the objectives, so essentially they are nothing but a lenses **and the** all have the capability of magnifying in different capacities. So, we do have objectives varying from 4 x, which means that the image which is actually seen through the microscope is 4 times the actual size of the object, all the way to about 150 x.

So, essentially there are about six objectives here. The way that this microscope operates its pretty simple, you have an illumination source, which is at the background, which is actually a UV source, it passes through a set of n d filters, neutral density filters which would cut half the U V light into different intensities. And then finally, the curve of light and the much lower intensity reaches this portion of the microscope, which has a what you know as filter tubes, so I like to explain what this filter tubes really do.

Essentially if you look at the way that the filter cube are assembled, these cubes have, you know **two** there are cubes which have two filters. Essentially what are filters? Filters



are essentially pieces of glasses, which are designed to cut off certain frequencies and let certain frequencies of light go passed it. So, in this particular filter cube as you see, there is emission filter, which is situated at the top, there is excitation filter, which is actually situated here, then we have some thing called dichroic mirror which is placed in between these cube in a just 45 degree angle. The purpose of the filter is essentially to take off the un necessary frequency from the UV, as I told you this microscope also has capability to florescence measurements, it is almost always important to be able to excite a certain di with a certain wavelengths of light. Let us say we have a di, which is excitable in the range of 390 nanometers wavelength.

So, I should have something, some cut off mechanism, where all the different components of the UV which are coming from the illumination source to this filter should get cut off except the 390 plus minus maybe about 20 nanometers. So, which is also known as a dichroic mirror, which is placed inside this filter cube, probably it is not visible from outside, but the way that that mirror operates is also based on this cut off principle.

So, there may be a cut off wavelength beyond which **the filter** the dichroic mirror may be able to refract the light and below which it should be able to reflect the light, so that is how these mirrors are typically designed, ok. Now, with this combination in mind, let us look at what is the optics, so this particular filter as you seeing here is going to face the UV light and it is going to take off the particular portion which is unimportant and sent or transmit the portion which is necessary for the particular florophore.

Now, each of these florophores are designed for a certain frequency and essentially they have an emission frequency range and an excitation frequency range, so what are cut off we used to correspond to the excitation frequency of the florophore? Once this is particular portion of light comes in the filter, it is reflected of the dichroic mirror which is now placed at 45 degrees angle and actually goes down this filter cube to the objective.

So, you have light beam coming from this end, cutting a portion of it through the filter and then the cut off portion, which is necessary portion goes on falls onto the 45 degrees mirror, which is placed in the center of the cube and it goes **the** reflected through the mirror because that is the property of the dichroic, ok.

So, let us say we are trying to cut off 390 plus minus 10 nanometers wave length band, so essentially we use a filter so that the particular package or the part of the package of light which comes out of the filter is from 380 to about 400 nanometers. And let us say we have a dichroic mirror which cuts off at 590, which means that anything below 590 is reflected of the mirror and anything above 590 is refracted of the mirror and it goes past the mirror.

So, now, just because the reflected beam goes down, it actually passes through this lower end of the filter cube and reaches through the objective onto the sample. This right here is the sample stage, it is x y z precisely moving stage, which is capable of positioning the sample with respect to the objective and we can actually **many** over the sample and see the portion of the zone which we want to focus and image.

So, essentially when the light goes and strikes the sample surface and there is a fluorophore, there is an emanation of a certain frequency, which is the emission frequency of the particular fluorophore. Now, this frequency actually would come back from the objective and come through this, hit the mirror. And here as you see, the dichroic it does us job again, in this case, because of **the** Stokes shift, the wavelengths that are generated by the fluorescence is actually higher on the higher side. And **so** suppose we have a fluorophore, we generates an emission frequency in the range of 620 nanometers may be, which is above the 590 cut off, thus provided by the dichroic.

So, what is the light beam which is going to come from the fluorophore through the objective is going to do is, to go past the mirror in the refraction mode and essentially you can pick it up using this other filter here, which can further streamline it to the band that we are looking at. So, anything above 590 is sent out and then we are trying to identify let us say a 620 plus minus 10 nanometers, which is about 610 to 630 nanometers region or band of the wavelength, which actually comes out and comes through the objective onto the eye piece and that is how you get the image.

Now, in a bright field dark field option, particularly for lithography, the problem that we faces, that we cannot image these silicon wafers **which are trans**, which are actually opaque using an inverted mechanism of light. In glass samples, glass holder or transparent or translucent samples, there is still possible, there is a light source here, in the microscope, which is actually white light as you can see, which can go past on the

sample surface if the sample is kept at this particular stage. However, in our case, if I put the silicon, if the silicon is opaque, the light will not be able to go past, so this is really not imaging modality we are looking at.

So, what we use is this principle of filter cubes and essentially we just remove the filters from both ends, so therefore it is just plain light which we are actually looking at for exciting and whatever is reflected off is captured. And essentially we can actually design the dichroic mirror in a manner that it actually gives only in the visible region of the spectrum and so typically we can see a mixed coloration, probably the white light, which is reflected off on the surface of this wafer and which comes out and gives a good feeling about what images on the particular sample.

Now, what the objective would also do is to try to blow up the image and make it well magnified and this very essential for micro features. We are looking at let say 26 microns feature or let us say 50 microns feature, as we probably know, **you know** all of you probably by the know that the human hair itself is about 100 microns, so we are talking about **a** half of that size, **of** we were talking sometimes about one tenth of that size, so it is not very easy to visualize until you really magnified to a certain extent and this is the tool which is to do that.

So, with background in mind, let us go ahead and try to do some imaging on the resists that we had actually processed that day. And so essentially I would like to close this filter cube and I would like to tell you now about how the image processing can actually be done using this particular imaging system, ok.

So, I am also going to show you now how we acquire these images digitally, of course through the eye piece. This is also known as the eye piece so which the image can be seen, because it is closer to the human eye that is why we call it eye piece. And essentially **what I am also** what I am now going to describe is **this** the way that we can digitally acquires this images and electronically sent at, so that we can have digital photographs.

So, one of the options that are available to us in this particular scope is this unit right here, which is also a charge coupled device a c c d camera. And essentially again this is probably finest form miniaturization that can happen using microelectronic processing technology. So, essentially whatever light intensity is allowed to passed the dichroics on

the filters, actually goes past this tube here and there is a small peltier cooled c c d chip which has the thousands of the, millions of this pixels, which are independent devices. So, the idea is as the intensity falls on these devices, the intensity of the light, there is a construction process is a generation of electrons from the photon and that gives you a signal, that gives you an aspect about what is the intensity, what are the different textual profiles from which the light has been reflected and that can be reconstructed simply to make what you call the real image. Of course, the magnification is done at down set here by the objective of the particular object.

So, the light goes pass into the c c d here, the charge coupled device here and electronically transfers, the data electronically transfers through this data cable as you are seen to a computer, which is placed right over. So, the data which is collected here electronically goes past this data cable all the way up to this computer here that you can see. And essentially in this computer, we do have a reader software, which actually also is able to acquire the data from the charge coupled device on the microscope and read it on this frame digitally using this particular software.

So, we have a licensed version of the software called image pro, which is used to identify the signal responses from the c c d camera and essentially I am just in about few minutes going to demonstrate how we can read out using the eye piece and how we can see here. Now, the advantage that the software also offers is that we do have a scaling mechanism here, where by feeding the particular scale factor, the magnification factor, we are able to generate cursor, which can give you dimensions as you join different points on the same image.

So, essentially I am going to describe this whole operation by starting with our sample, which is the spun codded exposed and developed for the microscope stage. This right here is the x y z stage, so I am going to actually go ahead and just simply place this wafer on this stage and kind of approximately center it. This being a bigger wafer, we do not have a clamping mechanism here, but essentially now what I am going to do is, to actually take this filter, set to number 4 option, which is actually the bright field option here and I already describe what bright field would mean essentially and then I am going to actually turn on the shutter, so that the light starts falling on the wafer surface here through the 4 x objective.

My goal now is to look into the eye piece and see how this image is being visualized on the top of this wafer. And yes, I can actually now see the images very clearly, which have come from the resist and I am going to actually transmit this data on to the c c d screen for **the for** your advantage, so that you can see it. And I am going to now also position the wafer in an area, where we can really have a good grasp and we can also have a scaling etcetera. So, this right here I have now a very well-focused object, I just changed the focus little bit and see if I can go any better, I think is pretty, **is probably,** is probably now a very well-focused onto the area.

The way that you focus these things is by lifting the stage up and down and going in the z direction. You have a leaber here and corresponding knob on the other side here, which you can rotate clock or anticlockwise for the z displacement to happen in the positive or the negative direction. And **you** what you need here is actually to look into scope into the eye piece and see that corresponding to what z distance is the image contrast the maximum, the image resolution the maximum. You will see that above **a** critical distance if you go any further the image becomes blurry, similarly below that distance **if** the image **you know** becomes **it becomes** blurry again; therefore we need to really ascertain the right z level for the correct focus to happen in this particular case.

Now, I am going to actually transmit and use the c c d camera to acquire what is there for your benefits, so that you can see what you did, what we did in our last experiment photolithography. So, for that what we need is basically try to use this leaber to open the shutter for this particular camera. Now, there were three options in this particular leaber as you can find out and this leader can actually come out and go back in, right.

So, essentially when the leaber is actually in its invert position, it only exposes the eye piece and you can only see the image, but you cannot really see it through the c c d camera, but if you're actually able to push it all the way to the more, the most outward position for this leaber, in that particular position, you can only expose the c c d camera and cut off the eye piece, so you cannot see anything anymore by this eye piece.

So, I am going to now transmits, now this the leaber being in this position, whatever is reflected of the surface of the wafer is getting transmitted through the c c d camera into the computer and I am now going to actually look at this image using the software, so that you can also have a grasp on that.

So, we **are** earlier open the image pro software. So, what I am going to do here is to go to this acquire menu and there are different options here in this particular software. The first option mentions video slash digital capture, so we actually **are able to...** so our purpose here is to get the digital image, although the capabilities of the systems are also to get real movies, particularly in a real time cases, where you may be capturing particles or it may be doing a reaction etcetera **within** with in a small architecture, so the capabilities of this particular microscope are enormous. So, what I am going do is to actually ask this microscope to digitally capture, so there is a menu which has been opened here, it is called cure imaging menu. And you have different options in this menu including the exposure preview, exposure acquisition and essentially you can also have an auto calculating option for the intensity, so that you can get a good grasp of the image.

So, I would actually be able to first see the preview here from this option and if I click on it as you see this, is really the image that I was wanting for you guys to see. This is something that we have developed using photolithography onto the surface of the wafer.

Now, I will be doing the dimensioning part just about the little bit, but what we need to do is to actually, suppose this is out of focus, in focus, you can actually change the focusing stage on the microscope as i told you, can be able to get a very good focus on these images. Now, this is probably one of the best **force** foreside that one can get using this image, because I have already calibrated using the eye piece, ok.

Now, I am going to actually store this image, so I go to the snap option here and automatically **of** autograph is generated **as** here as you can see, which actually gives you a digital image of what has been captured from the c c d camera. Now, regarding the scaling option, this actually a very easy way out to do scaling, so what I am going to do is to actually see what magnification we are using for this particular image. And as you may recall, the magnification that we had use a 4 x or this image is 4 times the actual size of the image that is there are on the feature.

So, I am going to actually go ahead and use the calibration tool, so you go to this option called measure, there is a calibration option and then I also want to somehow ask the software to identify that scale at which the image is being a processed.

So, the magnification value has to be put in the software for it to tell what really would be the actually image size, so whatever sizes is getting in terms of pixels on this digital

image would be converted by dividing by a factor of 4, so that the actual sizes can be obtained. So, I am going to actually go ahead and ask the system **the** or give the system magnification, so it is providing a standard magnification of 10 x, which is been the set value, but ours is 4 x, so we go to this drop down menu and actually go ahead and see our input, the reference calibration and make it 4 x and let the system understand it is 4 x. And then we have an option here of scale, which is actually having a text box, which says measure lengths and distances in the particular image.

So, I click on this option and scale comes up and then I am actually going to use the cursor and connect two points from end to end, to see what distances it would be talking about. So, let us say if I click on this edge of the image here, right here and go and click on this image edge here in this particular area, this distances corresponding to 127.9 microns, so 0.9 is actually relevant, so let us say it is about 128 microns.

So, this way we can actually get a very good feel of what the actual **you know** distance would be, so let us say we want to just connect this two points here on the small, **you know of this small** this piece here, so this corresponding to about 37 microns.

So, essentially you can actually measure say from here to here in this particular figure, this corresponds to about 187 microns, so you can actually very accurately and precisely measure the size of what has been generated. Mind you, this 37 microns is only one third the human hear dimension, so it is a real small entity to be seen with normalize, but this powerful imaging system or modality that we have enables us to actually see and measure what we have done. So, essentially I would like to actually go ahead and look at other areas, and let us actually save this image. So, we save changes to untitled, so we actually save by going to this snap option, so we take this as a snap, because you know we have done the measurements here, so even this needs to be snapped for saving properly.

So, we snap it and then go to file and save this as a certain **let us say** experimental photolithography one and use a save options here. So, this has been saved in the desktop, we can go, access it by just looking at this particular image here, it has been saved and you can see that this image is exactly is the same as we had done before, save before, so we can save these images digitally and use them to advantage.

So, what I am going to now do is to actually use a different area on the wafer and would like to show that how or what all features are there on the wafer surface. So, I again basically go to the acquire mode and use the video digital capture. And now, I am going to go and essentially do the preview mode, you can see this is what we had done before. And I am going to move off and let this shift to different places and you can see what all has been written in this particular **you know** domain.

So, let us actually go to a different area of the wafer, let us say we are talking about these channel like regions here, so these are essentially the circular channel like regions, **I would let we would** I am interested to find out what is the width of one of these, so these are actually trenches as you can see in the resist. And let us see what the width of one of this particular feature would be, so we again snap the image based on this, put it somewhere down here and then again do the calibration by selecting spatial scale, and calibrating it to 4 x. Mind you, the system actually gets back to the default 10 x every time we taken new image.

So, we have to actually be careful of feeding the exact magnification factor that we are using, we have not changed, so we are using a 4 x, so we make it calibrated again. We go to the scale option and let us look at the size of one of these channels, so this size really is about 125 microns. So, essentially let us also look at one of these edges, how these edges would look like, so they are again close to about that same 133 so 125 or 133 microns, so around 125 to 130 microns domain.

So, there are some other areas on the wafer, let us actually do the same option again to save it, we go to the snap tool and essentially save this file and make it experiment photolithography two option. So, you make two here, save this image close this particular image here and then let us go to a different area on the wafer and look at some other options.

So, if you look at something is written here on the on the resist and let us look at a different spot, where it may be a little visible in little better sense, we have to probably do some focusing in order to see what is actually written here. And let us actually focus, this is going out of focus, back to focus here and so, it is something like the inverted image of what was there on the mask, is **probably...** I can see this is the inverted c, this is the inverted e, inverted i s, and in this particular domain let us actually shift the wafer for



a little bit, so that we can exactly see what is on this. So, we actually move this wafer just about a little bit, can develop a thin film of metal on to a such a resist and then remove the areas where the resist was cross bonded or remain, or unbounded or remaining.

So, therefore, when that resist comes off, it takes off the metal also and the places of the vias or trenches or capillaries which were opened in between, where the silicon was exposed, the metal stays back. And you can use these techniques for developing thin interconnects on chips, especially in microelectronic chips. You can communicate electronically between two such islands or posts by having several 20 microns or 25 microns wires running in between. And this gives you tremendous advantage which can be used for sensing diagnostic signal transduction, so on and so forth.

So, basically photolithography can be considered to be one of the fundamental processes associated, the first step processes associated in realizing something at the microns scale; thank you.